

## Product Overview

### NDSH25170A: Silicon Carbide Schottky Diode 1700V, 25A, TO247

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### Features

- Max Junction Temperature
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

#### Benefits

- $T_j = 175^\circ\text{C}$
- Avalanche Rated 400 mJ

#### Applications

- SMPS
- Solar Inverter
- UPS
- Power Switching Circuits

#### End Products

- AUX Power Supply
- Rail Traction

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Device Grade	Configuration	$V_{RRM}$ (V)	$I_{F(ave)}$ (A)	$V_F$ (Max)	$I_{FSM}$ (A)	$I_R$ (Max) ( $\mu\text{A}$ )	Package Type
NDSH25170A	11.9997	Pb-free Halide free non AEC-Q and PPAP	Active	Commercial	Single	1700	35	1.75	220	40	TO-247-2LD

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